LITE-ON SEMICONDUCTOR

KBPC35005G(W) thru 3510G(W)

GLASS PASSIVATED BRIDGE RECTIFIERS

REVERSE VOLTAGE **- 50** to **1000** Volts
FORWARD CURRENT **- 35** Amperes

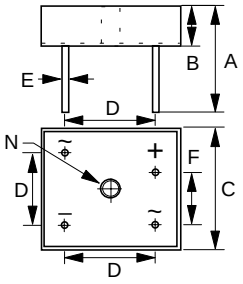
FEATURES

- Rating to 1000V PRV
- High efficiency
- Glass passivated chip junction
- Electrically isolated metal case for maximum heat dissipation
- UL recognized file # E95060

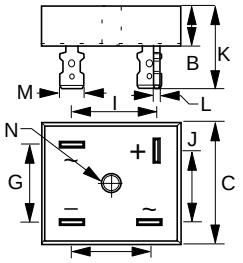
MECHANICAL DATA

- Case : Mounted in the bridge encapsulation
- Poarity : As marked on case
- Mounting : Hole for # 10 screw
- Weight : 0.85 ounces , 24.0 grams (terminal)
  : 0.74 ounces , 21.0 grams (wire)

KBPC-GW (Wire)



KBPC-G (Terminal)



KBPC-G/KBPC-GW		
DIM.	MIN.	MAX.
A	31.80	-
B	7.90	8.40
C	28.30	28.80
D	17.60	18.60
E	0.97	1.07
F	10.90	11.90
G	17.60	18.60
H	13.80	14.80
I	16.10	17.10
J	16.10	17.10
K	18.80	21.30
L	0.76	0.86
M	6.30	6.50
N	HOLE FOR NO. 10 SCREW	
	5.08	5.59
All Dimensions in millimeter		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	KBPC35 005G/W	KBPC35 01G/W	KBPC35 02G/W	KBPC35 04G/W	KBPC35 06G/W	KBPC35 08G/W	KBPC35 10G/W	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @T_C =55˚C	$I_{(AV)}$	35.0							A
Peak Forward Surge Current 8.3ms single half sine-wave super imposed on rated load (JEDEC METHOD)	I_{FSM}	400							A
Maximum forward Voltage at 17.5A DC	V_F	1.1							V
Maximum DC Reverse Current @T_J =25˚C at Rated DC Blocking Voltage @T_J =125˚C	I_R	5.0 500							uA
I^2t Rating for fusing (t < 8.3ms), (Note 1)	I^2t	660							A^2S
Typical Junction Capacitance per element (Note 2)	C_J	300							pF
Typical Thermal Resistance (Note 3)	$R_{\theta JC}$	1.4							˚C/W
Operating Temperature Range	T_J	-55 to +150							˚C
Storage Temperature Range	T_{STG}	-55 to +150							˚C

NOTES : 1.Measured at non-repetitive, for greater than 1ms and less than 8.3ms
2.Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
3.Device mounted on 300mm x 300mm x 1.6mm Cu Plate Heatsink.

REV. 2, 01-Dec-2000, KBDI03

FIG.1 - FORWARD CURRENT DERATING CURVE

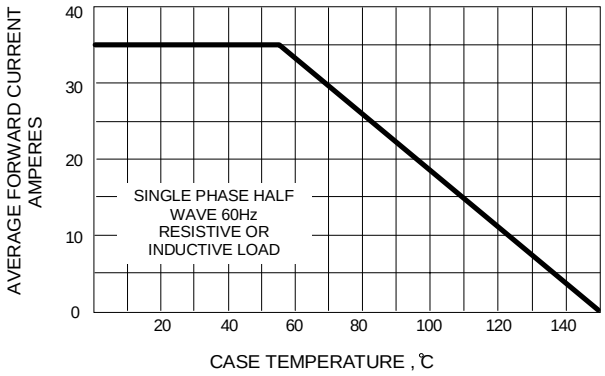


FIG.2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

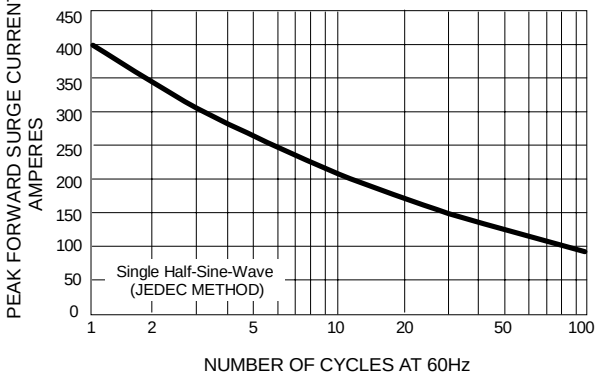


FIG.3 - TYPICAL JUNCTION CAPACITANCE

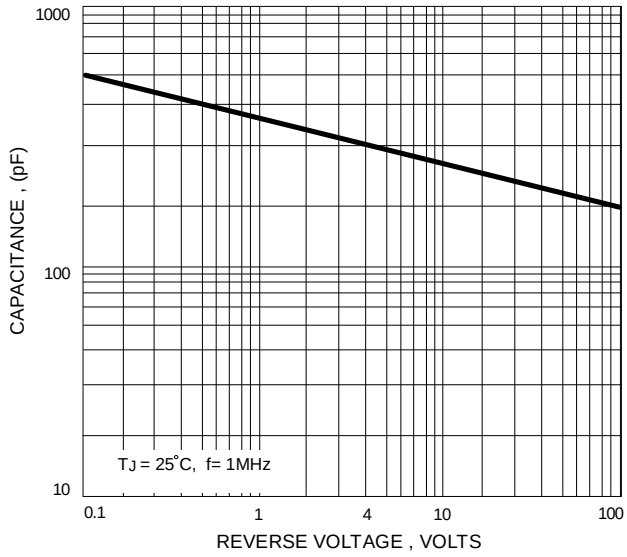


FIG.4 - TYPICAL FORWARD CHARACTERISTICS

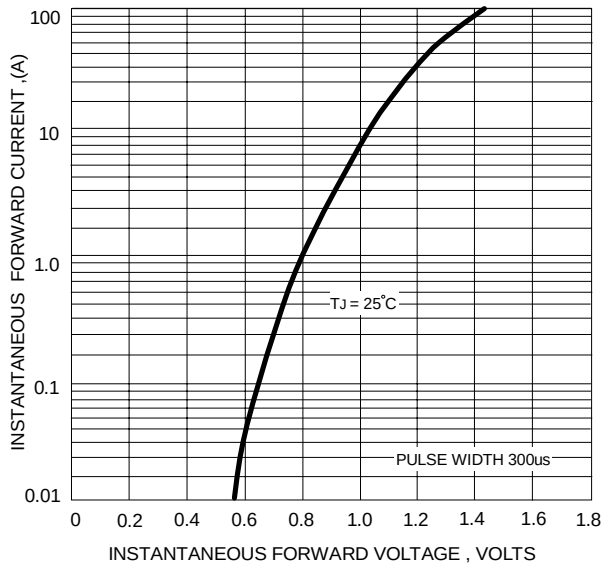


FIG.5 - TYPICAL REVERSE CHARACTERISTICS